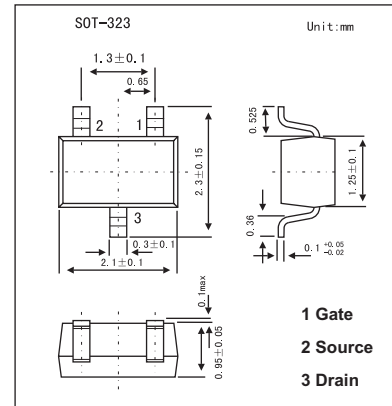
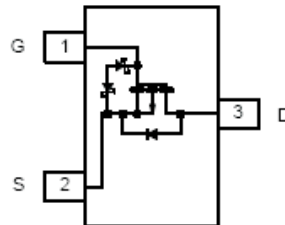


## P-Channel 2.5-V (G-S) MOSFET

## KI1303EDL

## ■ Features

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	5 secs	Steady State	Unit
Drain-source voltage	$V_{DS}$		-20	V
Gate-source voltage	$V_{GS}$		$\pm 12$	V
Continuous drain current ( $T_J = 150^\circ\text{C}$ )	$I_D$	$\pm 0.72$ $\pm 0.58$	$\pm 0.67$ $\pm 0.54$	A
				$T_A = 25^\circ\text{C}$ $T_A = 70^\circ\text{C}$
Pulsed drain current	$I_{DM}$	$\pm 2.5$		A
Continuous source current (diode conduction) *	$I_S$	-0.28	-0.24	A
Power dissipation *	$P_D$	0.34 0.22	0.29 0.19	W
				$T_A = 25^\circ\text{C}$ $T_A = 70^\circ\text{C}$
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150		$^\circ\text{C}$

\* Surface Mounted on 1" X 1" FR4 Board.

■ Thermal Resistance Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient*	$R_{thJA}$	$t \leq 5$ sec	315	375	$^\circ\text{C}/\text{W}$
		Steady State	360	430	
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	285	340		

\* Surface Mounted on 1" X 1" FR4 Board.

## KI1303EDL

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-0.6			V
Gate-body leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±4.5 V			±1	μA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V			-1	μA
		V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C			-5	
On-state drain current	I <sub>D(on)</sub>	V <sub>DS</sub> = -5 V, V <sub>GS</sub> = -4.5 V	1.5			A
Drain-source on-state resistance	r <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -1 A		0.360	0.430	Ω
		V <sub>GS</sub> = -3.6V, I <sub>D</sub> = -0.7 A		0.400	0.480	
		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -0.3 A		0.560	0.700	
Forward transconductance	g <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 A		1.7		S
Diode forward voltage	V <sub>SD</sub>	I <sub>S</sub> = -1 A, V <sub>GS</sub> = 0 V			-1.2	V
Total gate charge *	Q <sub>g</sub>	V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -1A		1.9	2.5	nC
Gate-source charge *	Q <sub>gs</sub>			0.45		
Gate-drain charge *	Q <sub>gd</sub>			0.44		
Turn-on time	t <sub>d(on)</sub>	V <sub>DD</sub> = -10V, R <sub>L</sub> = 10 Ω, I <sub>D</sub> = -1A, V <sub>GEN</sub> = -4.5V, R <sub>G</sub> = 6 Ω		180	300	ns
	t <sub>r</sub>			410	655	
Turn-off time	t <sub>d(off)</sub>			560	900	
	t <sub>f</sub>			530	850	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>		I <sub>F</sub> = -1 A, di/dt = 100 A/μs		435	

\* Pulse test: PW ≤ 300 μs duty cycle ≤ 2%.

## ■ Marking

Marking	LD
---------	----